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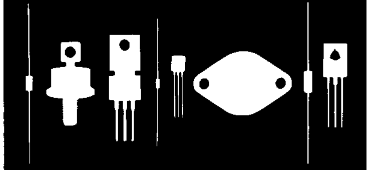


CBR10F-010P SERIES
CBR25F-010P SERIES
CBR35F-010P SERIES

FAST RECOVERY SILICON BRIDGE RECTIFIERS

10 THRU 35A, 100 THRU 600V

DESCRIPTION

- The CENTRAL SEMICONDUCTOR CBR10F, CBR25F, CBR35F series types are silicon single phase full wave bridge rectifiers designed for fast recovery applications.
- Standard recovery devices are also available .
- The plastic material used carries Underwriters Laboratory flammability classification 94V-0.
- Utilizes standard 0.25" fast on connectors.
- Wire leaded devices available by adding suffix "W" to part no. (ex: CBR35F-060PW).

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

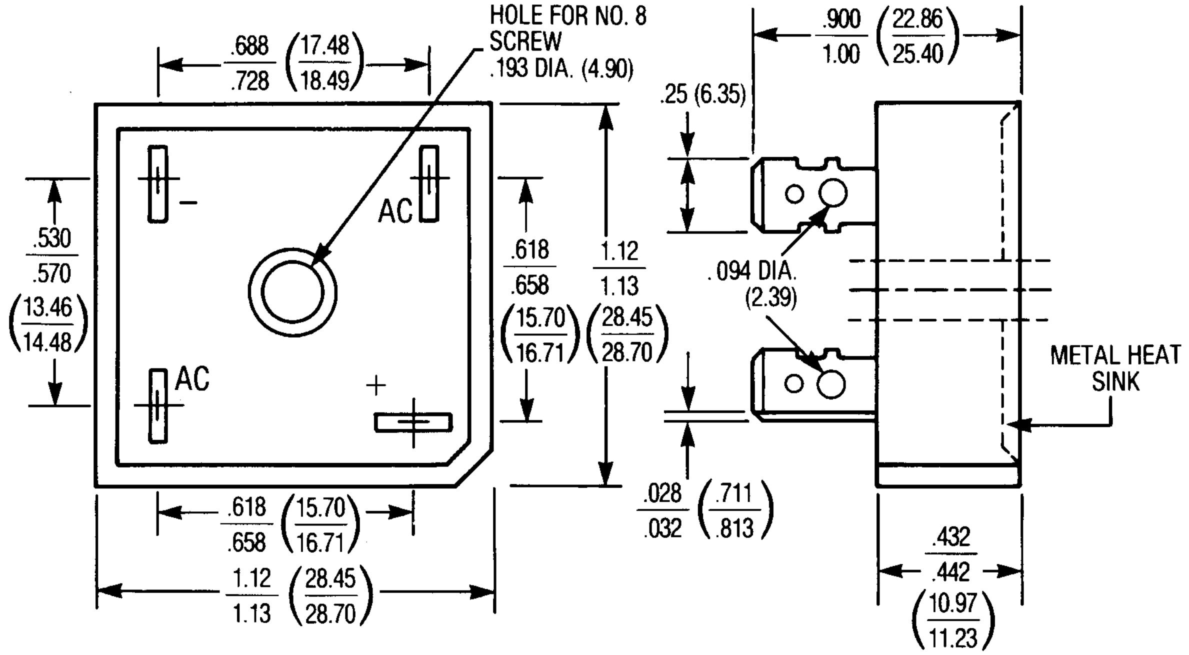
	SYMBOL	-010P	-020P	-040P	-060P	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	V
DC Blocking Voltage	V_R	100	200	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	V

		SYMBOL		UNIT
Average Forward Current (T_C=60°C)		I_O		
	CBR10F-010P SERIES		10	A
	CBR25F-010P SERIES		25	A
	CBR35F-010P SERIES		35	A
Peak Forward Surge Current (JEDEC)		I_{FSM}		
	CBR10F-010P SERIES		200	A
	CBR25F-010P SERIES		300	A
	CBR35F-010P SERIES		400	A
Operating and Storage Junction Temperature		T_J, T_{STG}	-65 to +150	°C
Maximum Thermal Resistance		ΘJC	1.5	°C/W
Isolation Voltage (case to leads)		V_{iso}	2500	Vac

ELECTRICAL CHARACTERISTICS (T_A=25°C)

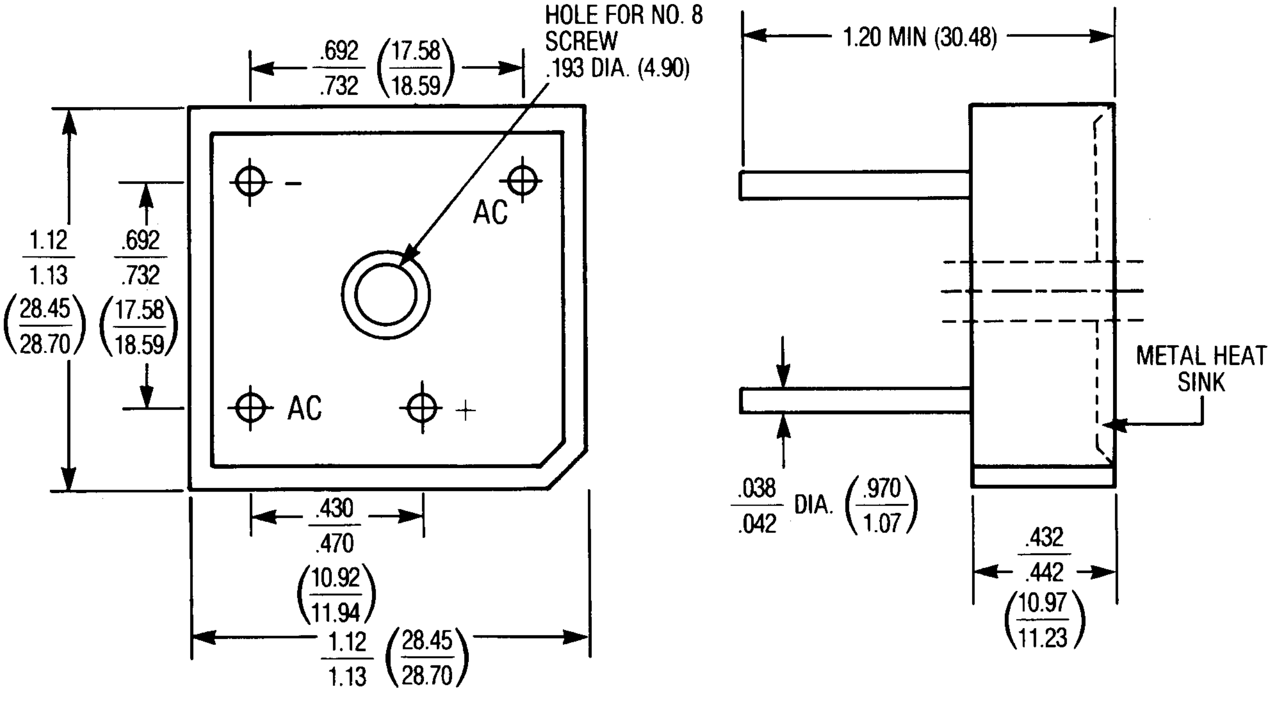
		MIN	MAX	UNIT
V_F	$I_F=\frac{1}{2}$ Rated I_O		1.3	V
I_R	V_R=Rated V_{RRM}		10	μA
t_{rr}	I_F=0.5A, I_R=1.0A, I_{rr}=0.25A (-010P thru -040P)		200	ns
t_{rr}	I_F=0.5A, I_R=1.0A, I_{rr}=0.25A (-060P)		350	ns

-010P SERIES



DIMENSIONS IN INCHES (MILLIMETERS)

-010PW SERIES



DIMENSIONS IN INCHES (MILLIMETERS)